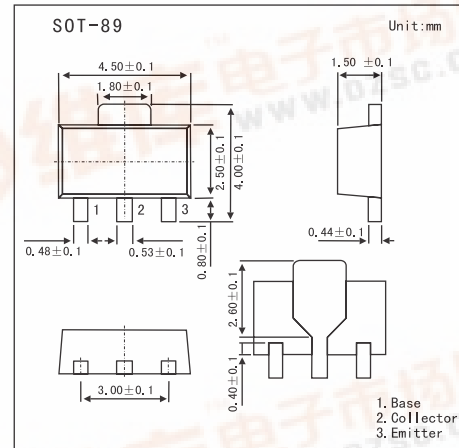


SMD Type Transistors

Low Frequency Transistor
2SC4672



Features

- Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A / 50mA$.
- Excellent DC current gain characteristics.

Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	3	A
	I_C (Pulse) *1	6	A
Collector power dissipation	P_C	0.5	W
	P_C *2	2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*1. Single pulse, $P_w = 10ms$

*2. $40 \times 40 \times 0.7mm$ Ceramic board

Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = 50\mu A$	60			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1mA$	50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 50\mu A$	6			V
Collector cutoff current	I_{CBO}	$V_{CB} = 60V$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5V$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 2V, I_C = 0.5A$	82		390	
		$V_{CE} = 2V, I_C = 1.5A$	45			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 50mA$		0.13	0.35	V
Output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0A, f = 1MHz$		25		pF
Transition frequency	f_T	$V_{CE} = 2V, I_E = -0.5A, f = 100MHz$		210		MHz

hFE Classification

Marking	DKP	DKQ	DKR
Rank	P	Q	R
hFE	82~180	120~270	180~390

